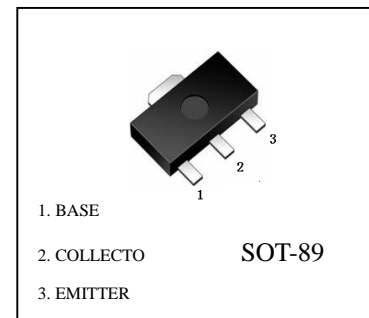


FEATURES

- $I_c = 1A$ Continuous Collector Current
- Low Saturation Voltage $V_{CE(sat)} < 500mV @ 0.5A$
- Epitaxial Planar Die Construction
- Complementary PNP types: BCX51, 52 and 53
- Halogen and Antimony Free. "Green" Devices

BCX54/55/56 (NPN)


Product	BCX54	BCX54-10	BCX54-16	BCX55	BCX55-10	BCX55-16	BCX56	BCX56-10	BCX56-16
Marking	BA	BC	BD	BE	BG	BM	BH	BK	BL

Maximum Ratings ($T_a=25\text{ }^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	BCX54	BCX55	BCX56	Unit
Collector-Base Voltage	V_{CBO}	45	60	100	V
Collector-Emitter Voltage	V_{CEO}	45	60	80	V
Emitter-Base Voltage	V_{EBO}	5			V
Continuous Collector Current	I_C	1			A
Peak Pulse Collector Current	I_{CM}	1.5			
Continuous Base Current	I_B	100			A
Peak Pulse Base Current	I_{BM}	200			
Power Dissipation (Note 1)	PD	1			W
Thermal Resistance, Junction to Ambient)	R_{JA}	124			$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150			$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (@ $T_a=25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
Collector-Base Breakdown Voltage	BCX54	45	-	-	V	$I_C = 100\mu\text{A}$	
	BCX55	60					
	BCX56	100					
Collector-Emitter Breakdown Voltage (Note 2)	BCX54	45	-	-	V	$I_C = 10\text{mA}$	
	BCX55	60					
	BCX56	80					
Emitter-Base Breakdown Voltage	$BVEBO$	5	-	-	V	$I_E = 10\mu\text{A}$	
Collector Cut-off Current	$ICBO$	-	-	0.1	μA	$V_{CB} = 30\text{V}$	
			-	20		$V_{CB} = 30\text{V}, T_A = 150^\circ\text{C}$	
Emitter Cut-off Current	$IEBO$	-	-	20	nA	$VEB = 4\text{V}$	
Static Forward Current Transfer Ratio (Note 2)	All versions	hFE	25	-	-		$I_C = 5\text{mA}, V_{CE} = 2\text{V}$
			40	-	250		$I_C = 150\text{mA}, V_{CE} = 2\text{V}$
			25	-	-		$I_C = 500\text{mA}, V_{CE} = 2\text{V}$
	10 gain grp	63	-	160		$I_C = 150\text{mA}, V_{CE} = 2\text{V}$	
	16 gain grp	100	-	250		$I_C = 150\text{mA}, V_{CE} = 2\text{V}$	
Collector-Emitter Saturation Voltage (Note 2)	$V_{CE(sat)}$	-	-	0.5	V	$I_C = 500\text{mA}, I_B = 50\text{mA}$	
Base-Emitter Turn-On Voltage (Note 2)	$V_{BE(on)}$	-	-	1.0	V	$I_C = 500\text{mA}, V_{CE} = 2\text{V}$	
Transition Frequency	fT	150	-	-	MHz	$I_C = 50\text{mA}, V_{CE} = 10\text{V}$ f = 100MHz	
Output Capacitance	C_{ob}	-	-	25	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$	

Notes: 1. For a device surface mounted on 25 mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

Notes: 2. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

BCX54/55/56 Typical Characteristics

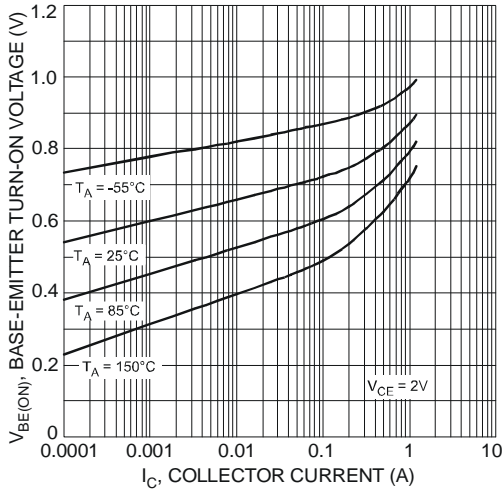


Fig. 3 Typical Base-Emitter Turn-On Voltage vs. Collector Current

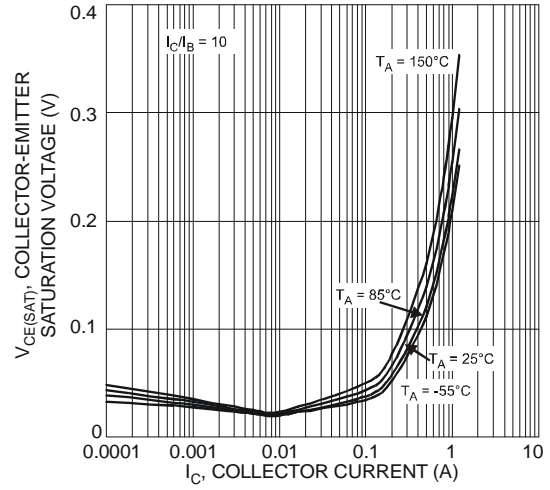


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

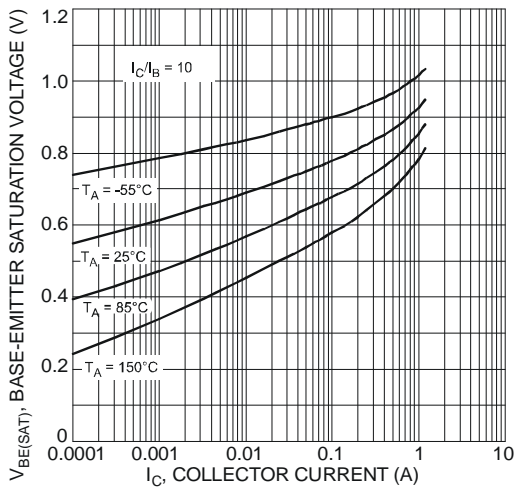


Fig. 5 Typical Base-Emitter Saturation Voltage vs. Collector Current

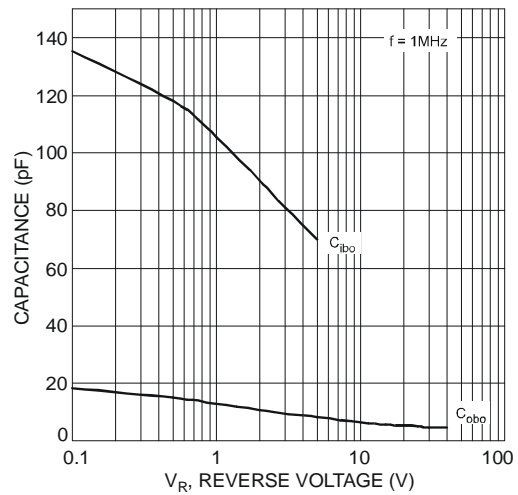


Fig. 6 Typical Capacitance Characteristics

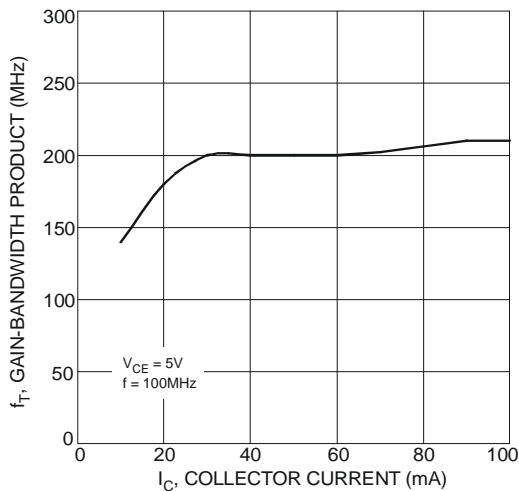


Fig. 7 Typical Gain-Bandwidth Product vs. Collector Current